

Erratum

Crystallization of bismuth titanate and bismuth silicate grown as thin films by atomic layer deposition [J. Crystal Growth 286 (2006) 376-383]

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In the original publication in the Figure 5 wrong XRD diagram was printed. The correct Figure 5 is:

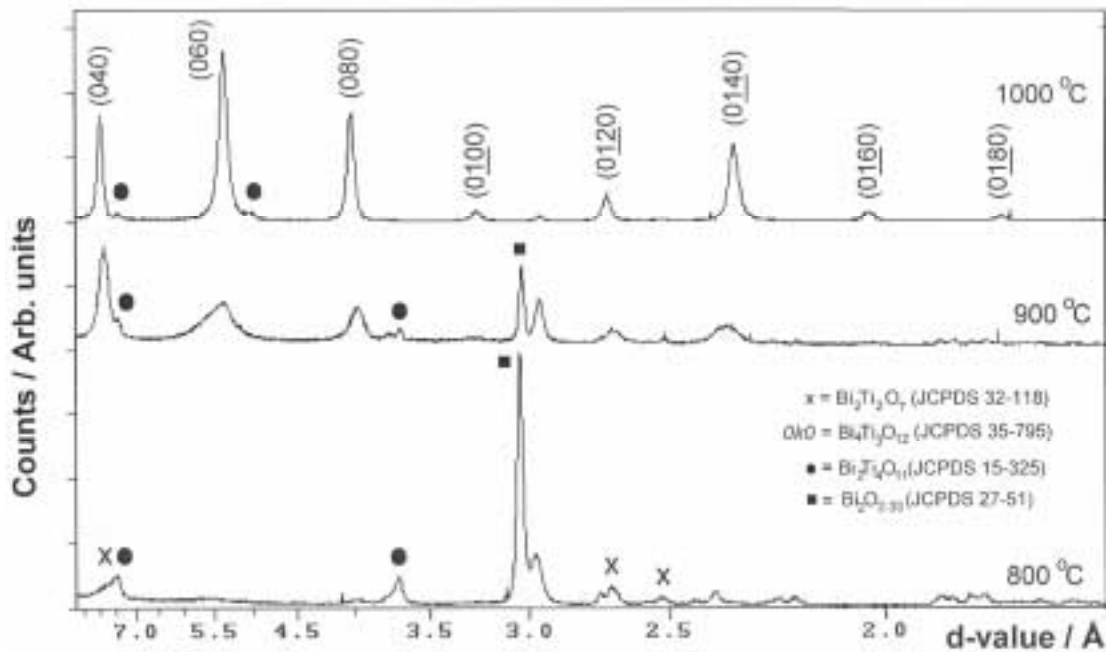


Fig. 5 XRD patterns of Bi-Ti-O thin films annealed at 800-1000 °C in N₂ atmosphere for 10 min. Bi-Ti-O films was deposited on Si(100) with pulsing ratio of 1:10 (Ti/Bi atomic ratio 0.28). Film thickness was 95 nm.

There is also small correction to the Figure caption 8. The correct caption is:

Figure 8. Backscattering spectra for 900 keV ^3He ions incident on the $825 \cdot 10^{15}$ at/cm² bismuth titanate sample as in Fig.7. For clarity, the insert shows only the depth distributions of Bi and Ti for the as grown and the 1000 °C annealed samples.